Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listings of Claims:

1. (original) A semiconductor die package comprising;
a semiconductor die;
a leadframe having a chemically-etched surface; and
a capsule enclosing said die and at least a portion said leadframe.

2. (original) The semiconductor package of Claim 1 wherein said leadframe consists essentially of copper alloy.

3. (original) A semiconductor die package comprising a semiconductor die, a leadframe having a roughened surface, and a capsule enclosing said die and at least a portion of said leadframe, wherein a surface of said leadframe is roughened by exposing said surface to a chemical etchant, thereby enhancing adhesion between said leadframe and said capsule.

4. (original) The semiconductor package of Claim 3 wherein said leadframe comprises copper alloy.

5. (original) The semiconductor package of Claim 4 wherein said chemical etchant comprises sulfuric acid.

6. (original) The semiconductor package of Claim 5 wherein said chemical etchant comprises hydrogen peroxide.

7. (currently amended) A ~~The~~ semiconductor package ~~of Claim 6~~ comprising:~~;~~
a semiconductor die;
a leadframe having a chemically-etched surface; and
a capsule enclosing said die and at least a portion said leadframe;
said package further comprising an organo-metallic coating ~~oxide~~ on the surface of the leadframe.

SILICON VALLEY
PATENT GROUP LLP
50 Mission College Blvd
Suite 360
Santa Clara, CA 95054
(408) 982-8200
FAX (408) 982-8210

8-20. (canceled)

21. (new) The semiconductor package of Claim 1 wherein the arithmetic mean deviation of a profile of said chemically-etched surface is in the range of 0.050 µm to 0.170 µm.

22. (new) The semiconductor package of Claim 21 wherein the mean peak-to-valley height of said chemically-etched surface is in the range of 0.180 µm to 0.700 µm.

23. (new) The semiconductor package of Claim 22 wherein the ten-point height of irregularities of said chemically-etched surface is in the range of 0.400 µm to 1.500 µm.

24. (new) The semiconductor package of Claim 21 wherein the ten-point height of irregularities of said chemically-etched surface is in the range of 0.400 µm to 1.500 µm.

25. (new) The semiconductor package of Claim 24 wherein the maximum profile valley depth of said chemically-etched surface is in the range of 0.200 µm to 0.750 µm.

27. (new) The semiconductor package of Claim 22 wherein the maximum profile valley depth of said chemically-etched surface is in the range of 0.200 µm to 0.750 µm.

27. (new) The semiconductor package of Claim 21 wherein the maximum profile valley depth of said chemically-etched surface is in the range of 0.200 µm to 0.750 µm.

28. (new) The semiconductor package of Claim 1 wherein the mean peak-to-valley height of said chemically-etched surface is in the range of 0.180 µm to 0.700 µm.

29. (new) The semiconductor package of Claim 28 wherein the ten-point height of irregularities of said chemically-etched surface is in the range of 0.400 µm to 1.500 µm.

30. (new) The semiconductor package of Claim 29 wherein the maximum profile valley depth of said chemically-etched surface is in the range of 0.200 µm to 0.750 µm.

31. (new) The semiconductor package of Claim 28 wherein the maximum profile valley depth of said chemically-etched surface is in the range of 0.200 µm to 0.750 µm.

32. (new) The semiconductor package of Claim 1 wherein the ten-point height of irregularities of said chemically-etched surface is in the range of 0.400 µm to 1.500 µm.

SILICON VALLEY
PATENT GROUP LLP
50 Mission College Blvd
Suite 360
Santa Clara, CA 95054
(408) 982-8200
FAX (408) 982-8210

33. (new) The semiconductor package of Claim 32 wherein the maximum profile valley depth of said chemically-etched surface is in the range of 0.200 µm to 0.750 µm.

34. (new) The semiconductor package of Claim 1 wherein the maximum profile valley depth of said chemically-etched surface is in the range of 0.200 µm to 0.750 µm.

35. (new) The semiconductor package of any one of Claims 21 to 34 further comprising an organo-metallic coating on the surface of the leadframe.

SILICON VALLEY
'ATENT GROUP LLP

50 Mission College Blvd
Suite 360
Santa Clara, CA 95054
(408) 982-8200
FAX (408) 982-8210